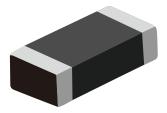


FEATURES

Fast response, instantly clamping the transient over	voltage.

- High surge current handling capability.
- High energy absorption capability.
- Low clamping voltages, providing better surge protection.
- Low capacitance values, providing digital switching circuitry protection.
- High insulation resistance, preventing electric arcing to the adjacent devices or circuits.



APPROVALS

	RoHS	Compliance with 2011/65/EU
	HF	Compliance with IEC61249-2-21:2003

APPLICATIONS

Offiversal Serial Dus (OSD).	Universal	Serial	Bus	(USB).
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Mobile communication.

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- Computer/DSP product.
- Video and audio ports.
- Portable/Hand-Held Products.
- Data, Diagnostic I/O ports.

ELECTRICAL SPECIFICATION

Test condition		
Varistor voltage	In = 1 mA DC	
Leakage current	Vdc = 5 V DC	
Maximum clamping voltage	lc = 1 A	
Rated peak single pulse transient current	8 / 20 µs waveform, +/- each 1 time induce	
Capacitance	10/1000 µs waveform	
Insulation resistance after reflow soldering	f = 1MHz, Vrms = 0.5 V	



ELECTRICAL SPECIFICATION

Electrical specification			
Maximum allowable continuous DC voltage	5	V	
trigger voltage / Varistor voltage / breakdown voltage	200	V	
Maximum clamping voltage	50	V	Maximum
Rated peak single pulse transient current	1	А	Maximum
Nonlinearity coefficient	> 12		
Leakage current at continuous DC voltage	< 0.05	uA	
Response time	< 0.5	ns	
Varistor voltage temperature coefficient	< 0.05	%/°C	
Capacitance measured at 1MHz	0.15	pF	Typical
Capacitance tolerance	-50 to +50	%	
Insulation resistance after reflow soldering on PCB	> 10	MΩ	
Operating ambient temperature	-55 to +125	°C	
Storage temperature	-55 to +125	°C	



RELIABILITY TESTING PROCEDURES

Reliability parameter		Test methods and remarks	Test requirement
Pulse current capability	lmax 8/20 µs	IEC 1051-1, Test 4.5. 10 pulses in the same direction at 2 pulses per minute at maximum peak current	d Vn ∕Vn≤10% no visible damage
Electrostatic discharge capability	ESD C=150 pF, R=330Ω	IEC 1000-4-2 Each 10 times in positive/negative direction in 10 sec at Air 15KV and 8KV contact discharge (Level 4)	d Vn ∕Vn≤10% no visible damage
	Thermal shock	IEC 68-2-14 Condition for 1 cycle Step 1 : Min. –40 °C, 30±3 min. Step 2 : Max. +125 °C, 30±3 min. Number of cycles: 30 times	d Vn ∕Vn≤5% no visible damage
	Low temperature	IEC 68-2-1 Place the chip at -40±5 °C for 1000±12hrs. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn ∕Vn≤5% no visible damage
Environmenta I reliability	High temperature	IEC 68-2-2 Place the chip at 125±5 °C for 1000± 24hrs. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn ∕Vn≤5% no visible damage
	Heat resistance	IEC 68-2-3 Apply the rated voltage for 1000±48hrs at 85±3 [°] C. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn ∕Vn≤5% no visible damage
	Humidity resistance	IEC 68-2-30 Place the chip at 40±2°C and 90 to 95% humidity for 1000±24hrs. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn ∕Vn≤10% no visible damage
	Pressure cooker test	Place the chip at 2 atm, 120 °C , 85%RH for 60 hrs. Remove and place for 24 \pm 2hrs at room temp. condition, then measure	d Vn ∕Vn≤10% no visible damage
	Operating life	Apply the rated voltage for 1000±48hrs at 125±3 °C. Remove and place for 24±2hrs at room temp. condition, then measure	d Vn ∕Vn≤10% no visible damage
Mechanical Reliability	Adhesive strength	IEC 68-2-22 Applied force on SMD chip by fracture from PCB	Strength>10 N no visible damage



MATERIAL SPECIFICATION

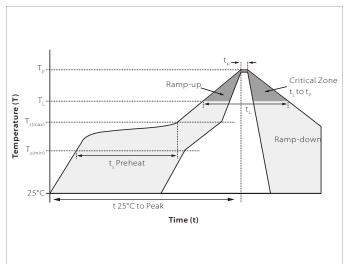
Body	Internal electrode	External electrode	Thickness of Ni/Sn plating layer
ZnO based ceramics	Silver – Palladium	Silver – Nickel – Tin	Nickel > 1 μ m, Tin > 2 μ m

DIMENSION SPECIFICATION



SOLDERING RECOMMENDATIONS

	Reflow Condition	Lead-free assembly
	Temperature Max (T _{s(min)})	150°C
Pre Heat	Temperature Max (T _{s(max)})	200°C
	Time (min to max) (t_s)	60 – 180 secs
Average ra	mp up rate (Liquidus Temp (T_L) to peak	3°C/second max
	$T_{s(max)}$ to T_{L} - Ramp-up Rate	3°C/second max
Reflow	Temperature (T _L) (Liquidus)	217°C
Kenow	Time (min to max) (t _{$l)$}	60 – 150 seconds
PeakTem	perature (T _p)	260°C
Time with	iin 5°C of actual peak Temperature (t _p)	20 – 40 seconds
Ramp-dc	own Rate	6°C/second max
Time 25°	C to peak Temperature (T _p)	8 minutes max.
Do not ex	kceed	260°C





DRDERING INF ORMATIOON

Part Number	Package&Size	QTY/Reel	Reel Size
SME0402B5.0UA	0402 (1.0 x 0.5 mm)	10000PCS	7″



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